

FH38P03G6

P-Channel Enhancement Mode MOSFET

Description

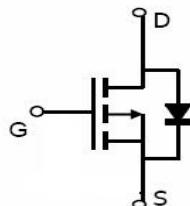
The FH38P03G6 is the P-Channel enhancement mode MOSFET in a plastic package (PDFN3.3x3.3-8L) using the Trench technology.

Applications

- ◆ High Speed Switch
- ◆ DC-DC Converters
- ◆ Lithium-Ion Battery

Features

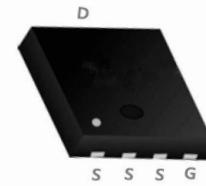
- ◆ $V_{DS} = -30V$; $I_D = -38A$
- ◆ $R_{DS(ON)}(\text{Typ.}) = 8.5\text{ m}\Omega$ @ $V_{GS} = -10V$
- ◆ $R_{DS(ON)}(\text{Typ.}) = 11\text{ m}\Omega$ @ $V_{GS} = -4.5V$
- ◆ Logic Level Compatible
- ◆ SMD Package (PDFN3.3x3.3-8L)
- ◆ Trench Technology
- ◆ Fast Switching



Schematic diagram



Marking and Pin Assignment



PDFN3.3x3.3-8L top view

Absolute Maximum Ratings ($T_A = 25^\circ C$, unless otherwise specified)

Parameter	Symbol	Typical	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ($T_C = 25^\circ C$)	I_D	-38	A
Pulsed Drain Current (Note 3)	I_{DM}	-100	A
Power Dissipation	P_D	31	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	°C
Thermal Resistance-Junction to Ambient (Note 1)	R_{thJA}	80	°C/W

■ Electrical Characteristics ($T_A = 25^\circ\text{C}$, unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Drain-source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}} = 0\text{V}, I_{\text{D}} = -250\mu\text{A}$	-30	-34	-	V
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_{\text{D}} = -250\mu\text{A}$	-1.1	-1.5	-1.9	V
Gate-Body Leakage Current	I_{GSS}	$V_{\text{DS}} = 0\text{V}, V_{\text{GS}} = \pm 20\text{V}$	-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}} = -30\text{V}, V_{\text{GS}} = 0\text{V}$	-	-	-1	μA
Drain-Source On-Resistance	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = -10\text{V}, I_{\text{D}} = -10\text{A}$	-	8.5	11	$\text{m}\Omega$
		$V_{\text{GS}} = -4.5\text{V}, I_{\text{D}} = -8.0\text{A}$	-	11	14	
Forward Transconductance	g_{FS}	$V_{\text{DS}} = -5\text{V}, I_{\text{D}} = -5.0\text{A}$	-	15		S
Diode Forward Voltage (Note 2)	V_{SD}	$V_{\text{GS}} = 0\text{V}, I_{\text{S}} = -1.0\text{A}$	-	-	-1.2	V
Diode Forward Current (Note 1)	I_{S}		-	-	-10	A
Dynamic						
Total Gate Charge	Q_g	$V_{\text{DS}} = -15\text{V}, V_{\text{GS}} = -10\text{V}, I_{\text{D}} = -1\text{A}$	-	45	-	nC
Gate-Source Charge	Q_{gs}		-	5	-	
Gate-Drain Charge	Q_{gd}		-	4	-	
Input Capacitance	C_{iss}	$V_{\text{DS}} = -15\text{V}, V_{\text{GS}} = 0\text{V}, f = 1\text{MHz}$	-	1970	-	pF
Output Capacitance	C_{oss}		-	250	-	
Reverse Transfer Capacitance	C_{rss}		-	164	-	
Switching						
Turn-On Delay Time	$t_{\text{d(on)}}$	$V_{\text{DD}} = -15\text{V}, R_{\text{L}} = 15\Omega, I_{\text{D}} = -1\text{A}, V_{\text{GS}} = -4.5\text{V}, R_{\text{GEN}} = 10\Omega$	-	9	-	nS
Rise Time	t_r		-	5	-	
Turn-Off Delay Time	$t_{\text{d(off)}}$		-	38	-	
Fall-Time	t_f		-	11	-	

- Note:
1. Mounted on FR4 board, $t \leq 5\text{sec}$.
 2. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.
 3. Repetitive Rating: Pulse width limited by maximum junction temperature.

■ Typical Electrical and Thermal Characteristics

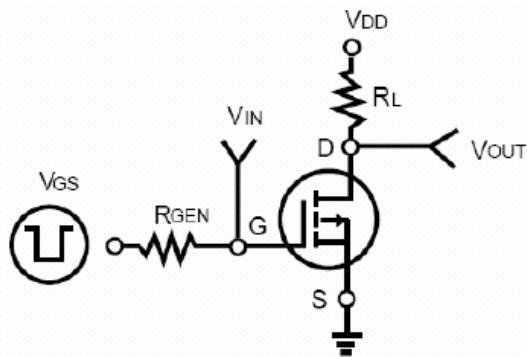


Figure 1: Switching Test Circuit

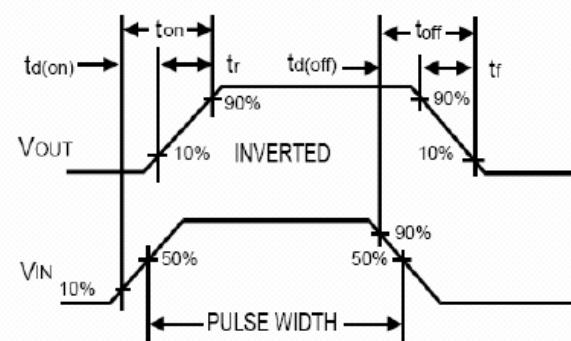


Figure 2: Switching Waveforms

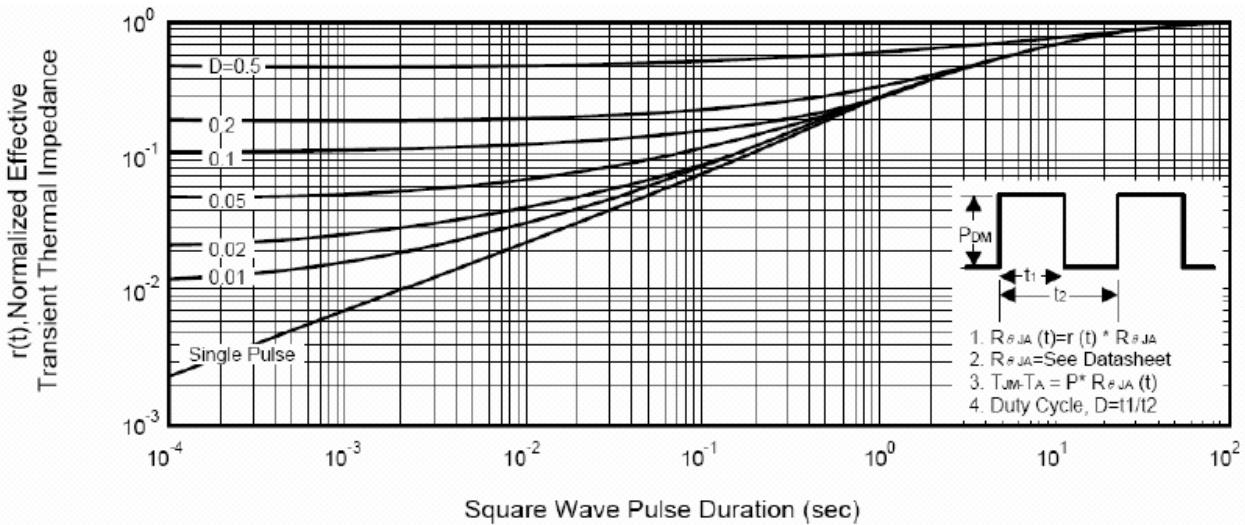
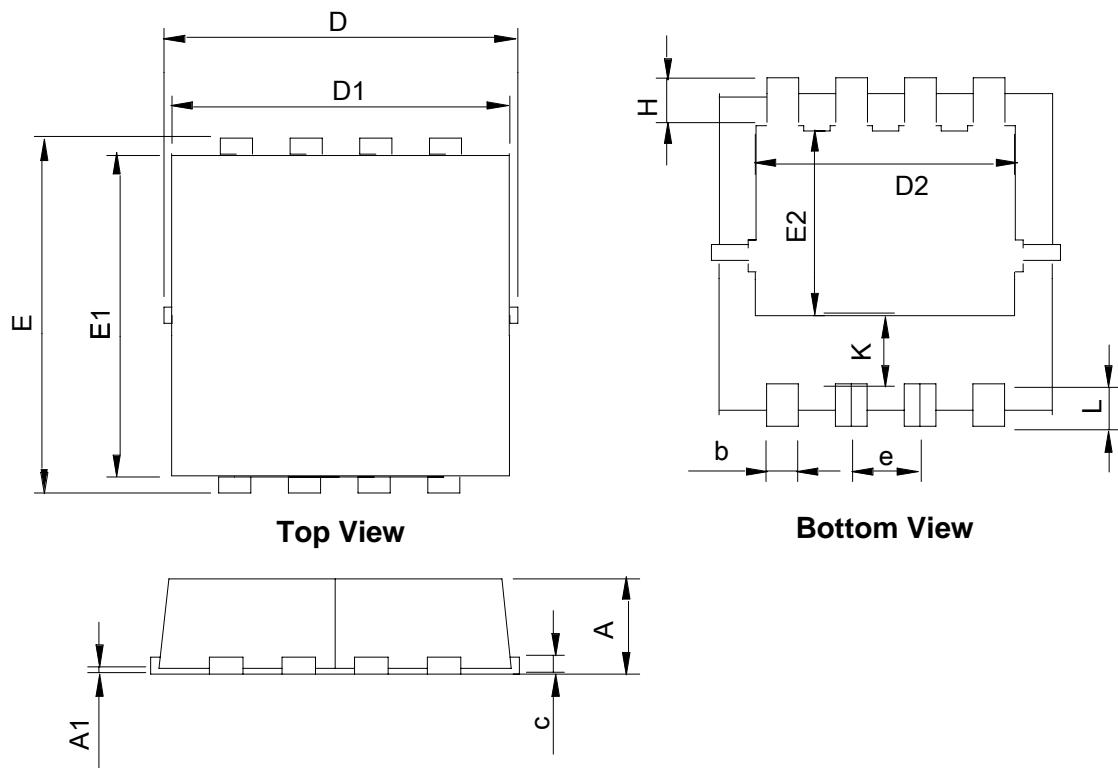


Figure 3: Normalized Maximum Transient Thermal Impedance

■ Package Dimensions : PDFN3.3x3.3-8L

SYMBOL	PDFN3.3x3.3-8L			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	0.70	1.00	0.028	0.039
A1	0.00	0.05	0.000	0.002
b	0.25	0.35	0.010	0.014
c	0.14	0.20	0.006	0.008
D	3.10	3.50	0.122	0.138
D1	3.05	3.25	0.120	0.128
D2	2.35	2.55	0.093	0.100
E	3.10	3.50	0.122	0.138
E1	2.90	3.10	0.114	0.122
E2	1.64	1.84	0.065	0.072
e	0.65 BSC		0.026 BSC	
H	0.32	0.52	0.013	0.020
K	0.59	0.79	0.023	0.031
L	0.25	0.55	0.010	0.022

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